

ABSTRACT

A substrate patterning integration is disclosed to address structural and process limitations of conventional resist patterning over hardmask techniques. A resist layer positioned adjacent a substrate layer is patterned, subsequent to which a hardmask layer is deposited. The hardmask layer may be thinned to expose remaining portions of the patterned resist layer for removal by chemical treatment to expose portions of the underlying substrate layer into which the pattern may be transferred using wet or dry chemical etch techniques.